

■ **FEATURES**

- UL recognition, file #E230084
- Glass passivated chip junction
- Thin single in-line package
- High surge current capability
- Solder dip 275 °C max. 7 s, per JESD 22-B106

■ **TYPICAL APPLICATIONS**

General purpose use in AC/DC bridge full wave rectification for switching power supply, home appliances, office equipment, industrial automation applications.

■ **MECHANICAL DATA**

- **Package:** JB
Molding compound meets UL 94 V-0 flammability rating, RoHS-compliant, Halogen free
- **Terminals:** Tin plated leads, solderable per J-STD-002 and JESD22-B102
- **Polarity:** As marked on body

■ **MAXIMUM RATINGS** ($T_a=25^{\circ}\text{C}$ Unless otherwise specified)

PARAMETER	SYMBOL	UNIT	D4JB05	D4JB10	D4JB20	D4JB40	D4JB60	D4JB80	D4JB100
Device marking code			D4JB05	D4JB10	D4JB20	D4JB40	D4JB60	D4JB80	D4JB100
Maximum Repetitive Peak Reverse Voltage	VRRM	V	50	100	200	400	600	800	1000
Maximum RMS Voltage	VRMS	V	35	70	140	280	420	560	700
Maximum DC blocking Voltage	VDC	V	50	100	200	400	600	800	1000
Average Rectified Output Current @60Hz sine wave, R-load,	With heatsink $T_c = 122^{\circ}\text{C}$	IO	A	4.0					
	Without heatsink $T_a = 25^{\circ}\text{C}$			2.3					
Forward Surge Current (Non-repetitive) @60Hz Half-sine wave, 1 cycle, $T_j=25^{\circ}\text{C}$	IFSM	A	135						
Forward Surge Current (Non-repetitive) @1ms, square wave, 1 cycle, $T_j=25^{\circ}\text{C}$			270						
Current squared time @1ms $\leq t \leq 8.3$ ms $T_j=25^{\circ}\text{C}$, rating of per diode	I ² t	A ² S	75.6						
Storage temperature	T _{stg}	°C	-55 ~ +150						
Junction temperature	T _j	°C	-55 ~ +150						
Dielectric strength @ Terminals to case, AC 1 minute	V _{dis}	KV	2						
Mounting torque @Recommend torque: 5kg·cm	Tor	kg·cm	8						

■ **ELECTRICAL CHARACTERISTICS** ($T_a=25^\circ\text{C}$ Unless otherwise specified)

PARAMETER	SYMBOL	UNIT	TEST CONDITIONS	D4JB05	D4JB10	D4JB20	D4JB40	D4JB60	D4JB80	D4JB100
Maximum instantaneous forward voltage drop per diode	V_F	V	$I_{FM}=2.0A$	1.0						
Maximum DC reverse current at rated DC blocking voltage per diode	I_R	μA	$T_j=25^\circ\text{C}$	5						
			$T_j=125^\circ\text{C}$	100						
Typical junction capacitance	C_j	μF	Measured at 1MHz and Applied Reverse Voltage of 4.0 V.D.C	38						

■ **THERMAL CHARACTERISTICS** ($T_a=25^\circ\text{C}$ Unless otherwise specified)

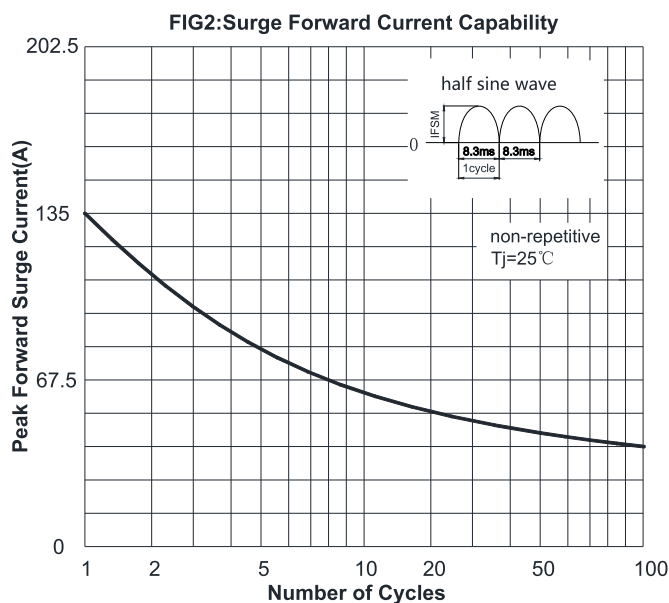
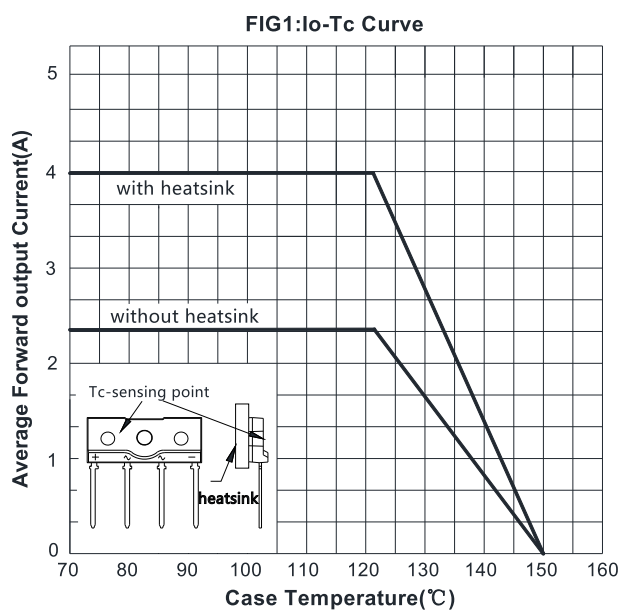
PARAMETER		SYMBOL	UNIT	D4JB05	D4JB10	D4JB20	D4JB40	D4JB60	D4JB80	D4JB100
Thermal Resistance	Between junction and ambient, Without heatsink	$R_{\theta J-A}$	$^\circ\text{C/W}$	28.0						
	Between junction and case, With heatsink	$R_{\theta J-C}$		3.5						

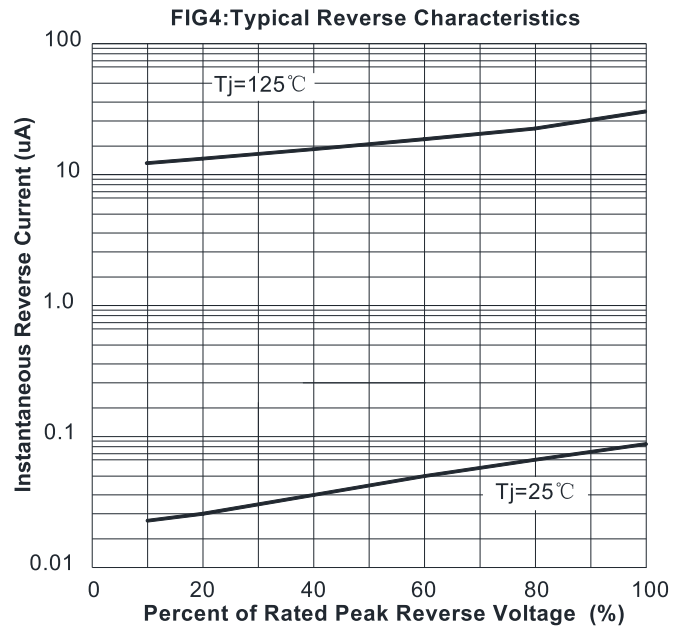
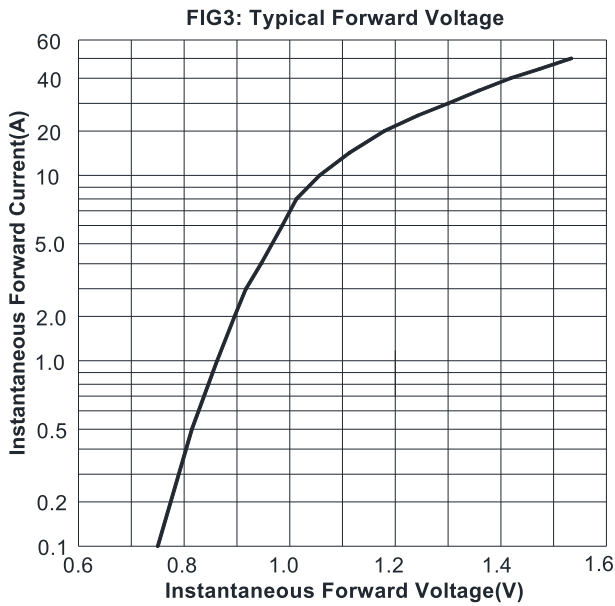
Note: Device mounted on 75mm x 45mm x 5.5mm Aluminum Plate Heatsink.

■ **PACKAGING INFORMATION**

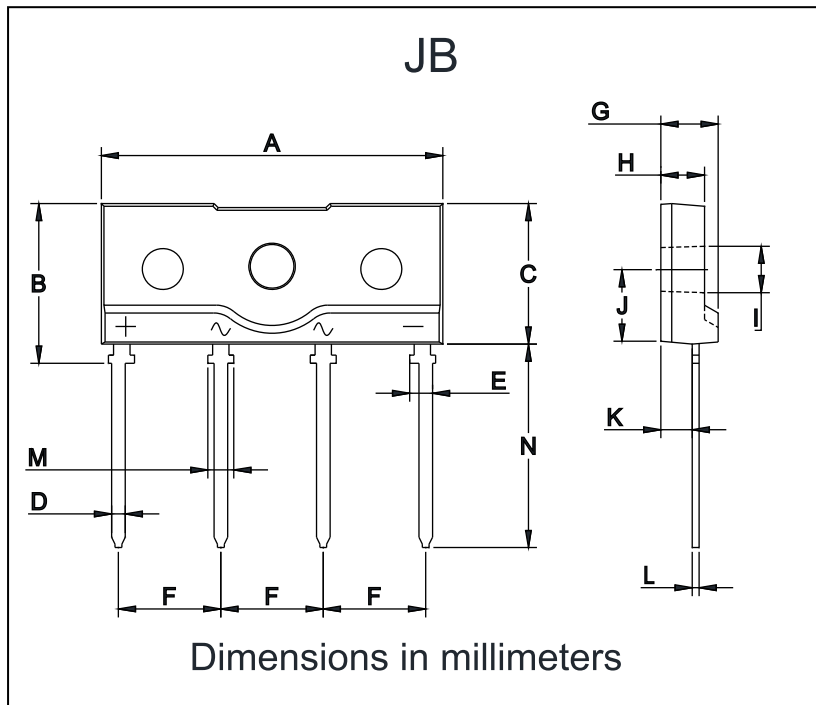
PREFERRED P/N	PACKAGE CODE	UNIT WEIGHT(g)	MINIMUM PACKAGE(pcs)	INNER BOX QUANTITY(pcs)	OUTER CARTON QUANTITY(pcs)	DELIVERY MODE
D4JB05 ~ D4JB100	B1	Approximate 2.4	20	1000	2000	Tube

■ **CHARACTERISTICS (TYPICAL)**





■ **OUTLINE DIMENSIONS**



JB		
Dim	Min	Max
A	24.7	25.3
B	11.4	12.0
C	10.0	10.6
D	0.9	1.1
E	1.75(MAX)	
F	7.3	7.7
G	3.9	4.5
H	2.9	3.9
I	3.1	3.4
J	5.4	6.0
K	2.0	2.6
L	0.4	0.6
M	2.1	2.3
N	14.6	15.2